



Fig. 1
(PRIOR ART)

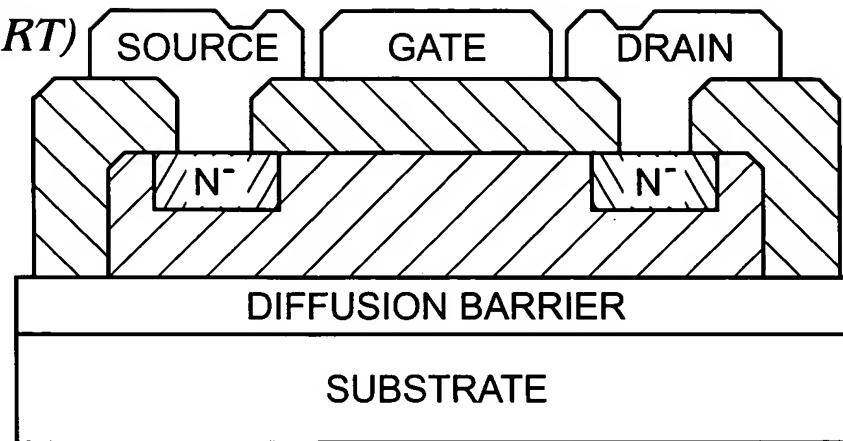


Fig. 2

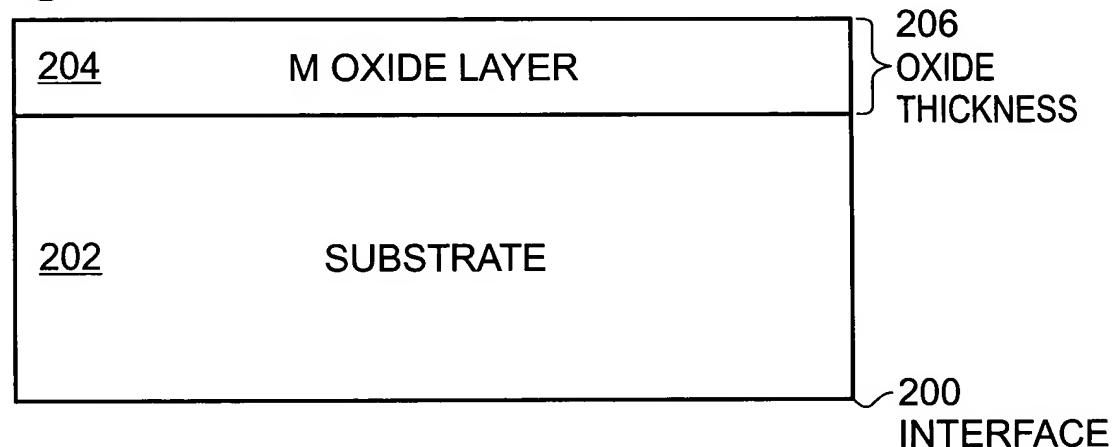


Fig. 3

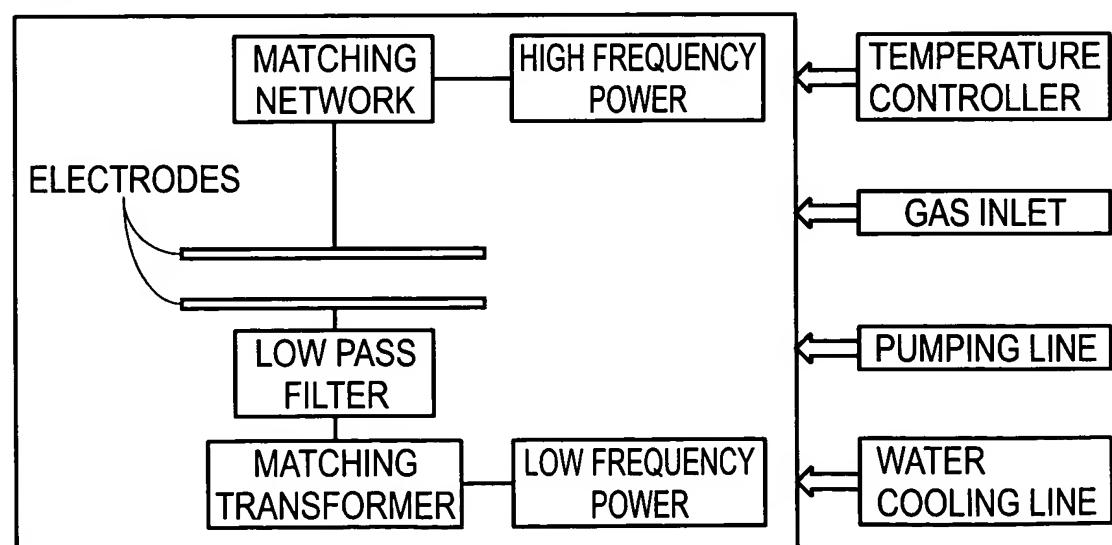




Fig. 4

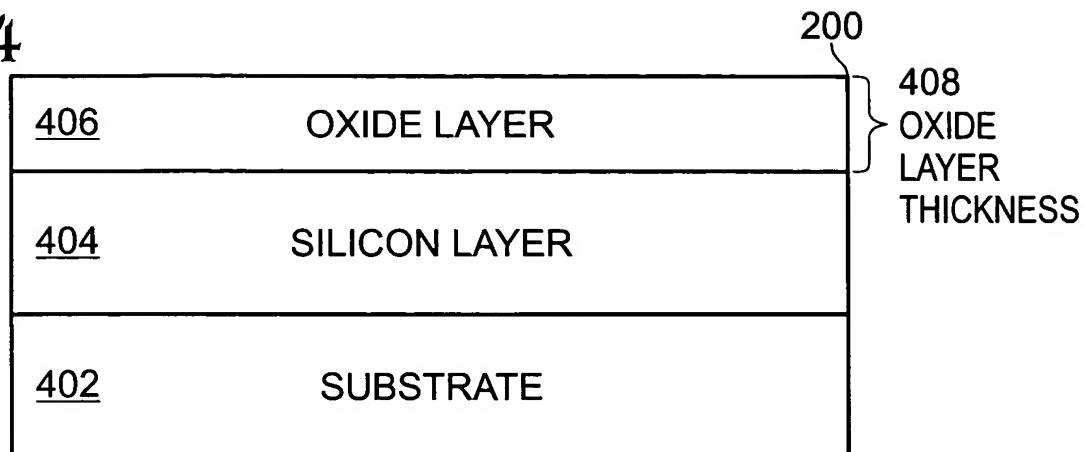


Fig. 5

T _{dep} (°C)	d (Å)	PLASMA	V _{FB} (V)	N _f (cm ⁻²)	D _{it} (cm ⁻² eV ⁻¹)	J (A/cm ²)	E (MV/cm)	E _{BD} (MV/cm)
		OXIDATION		(X10 ¹¹ cm ⁻²)	(X10 ¹⁰ cm ⁻² eV ⁻¹)	(AT 2 MV/cm)	(AT J=10 ⁻⁸ A/cm ²)	(PHYSICAL)
150	500	As-Dep	-7.5	26.0	3.5	1.80E-07	4.3	6.8
150	500	He/O ₂	-0.8	1.8	1.2	2.60E-08	8.4	7.2

TABLE 1

HD-PECVD SiO₂ THIN FILMS DEPOSITED AT 150°C

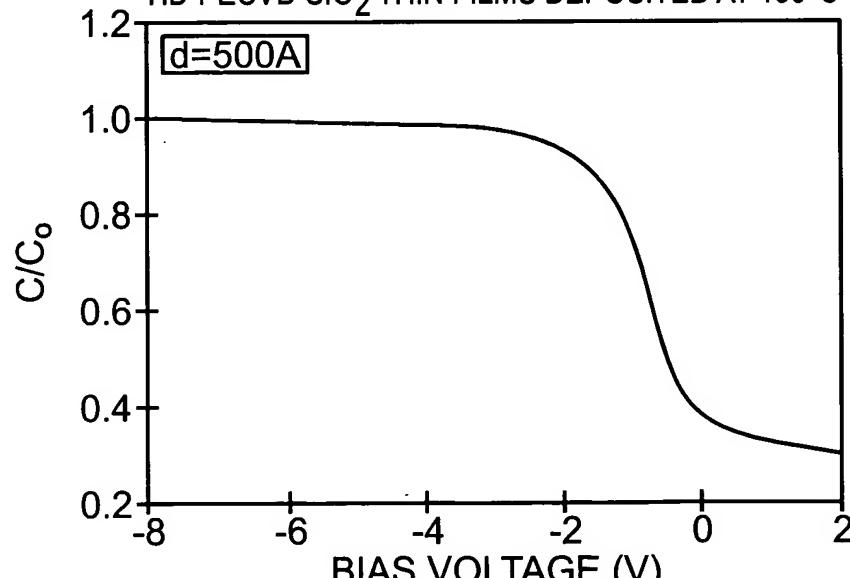


TABLE 2



Fig. 6

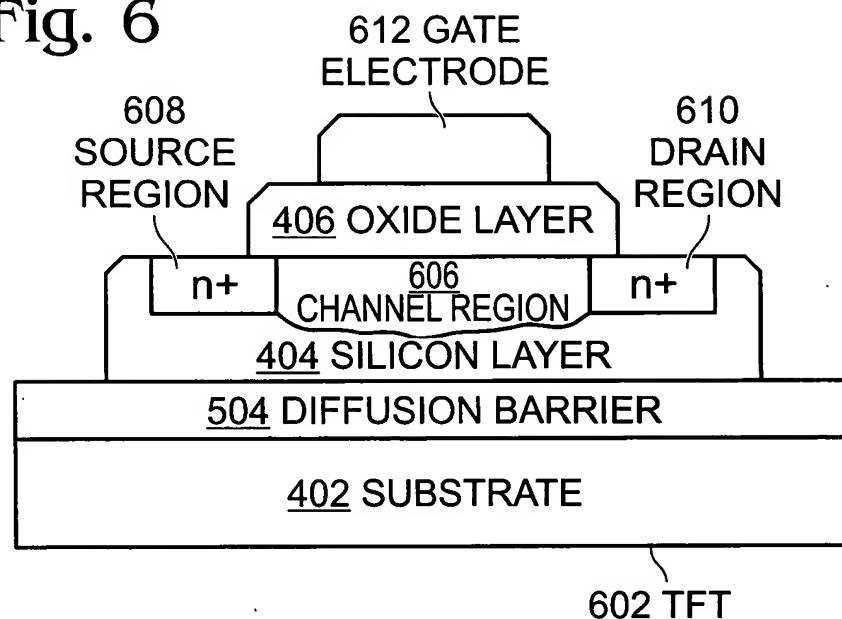




Fig. 7

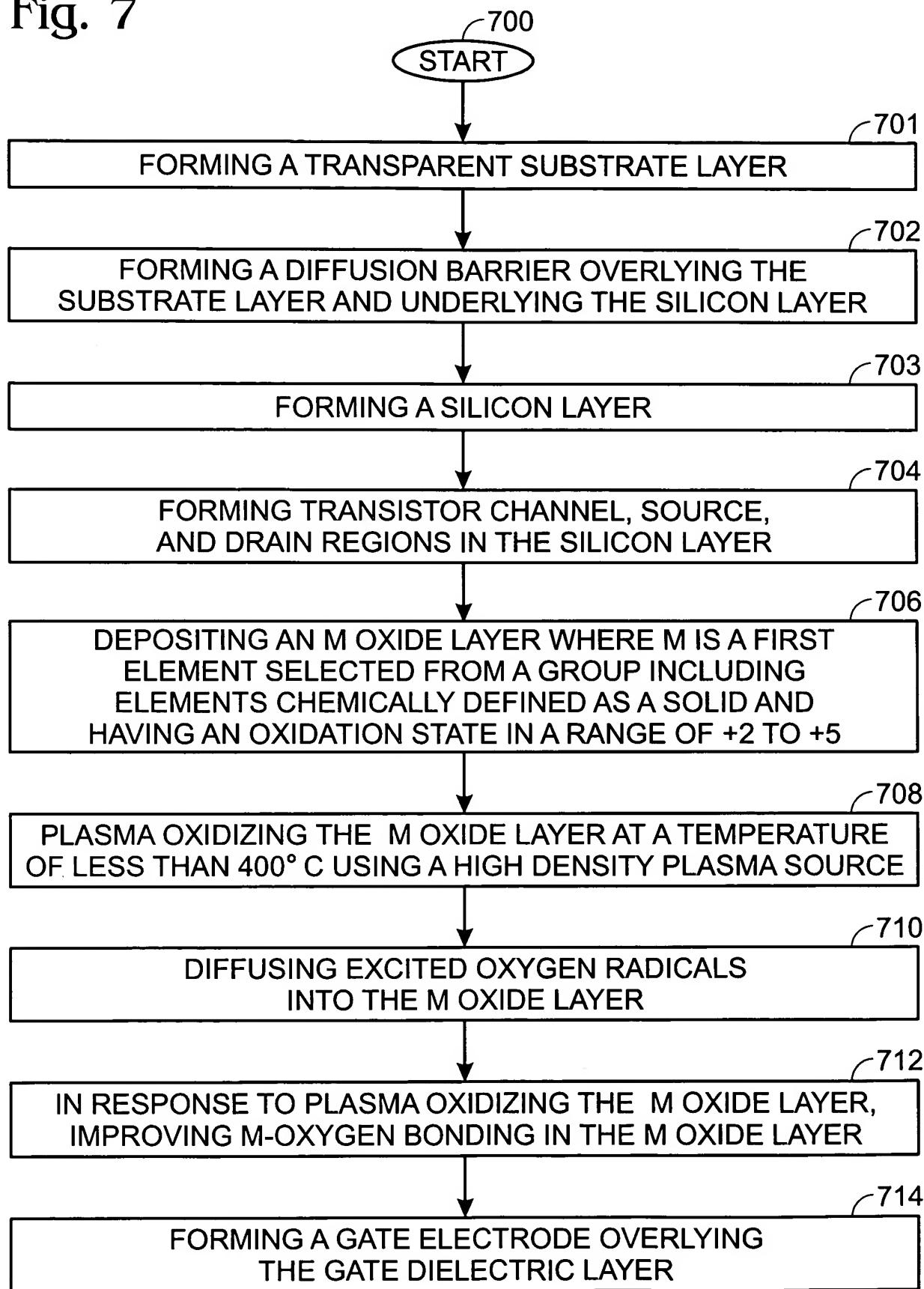




Fig. 8

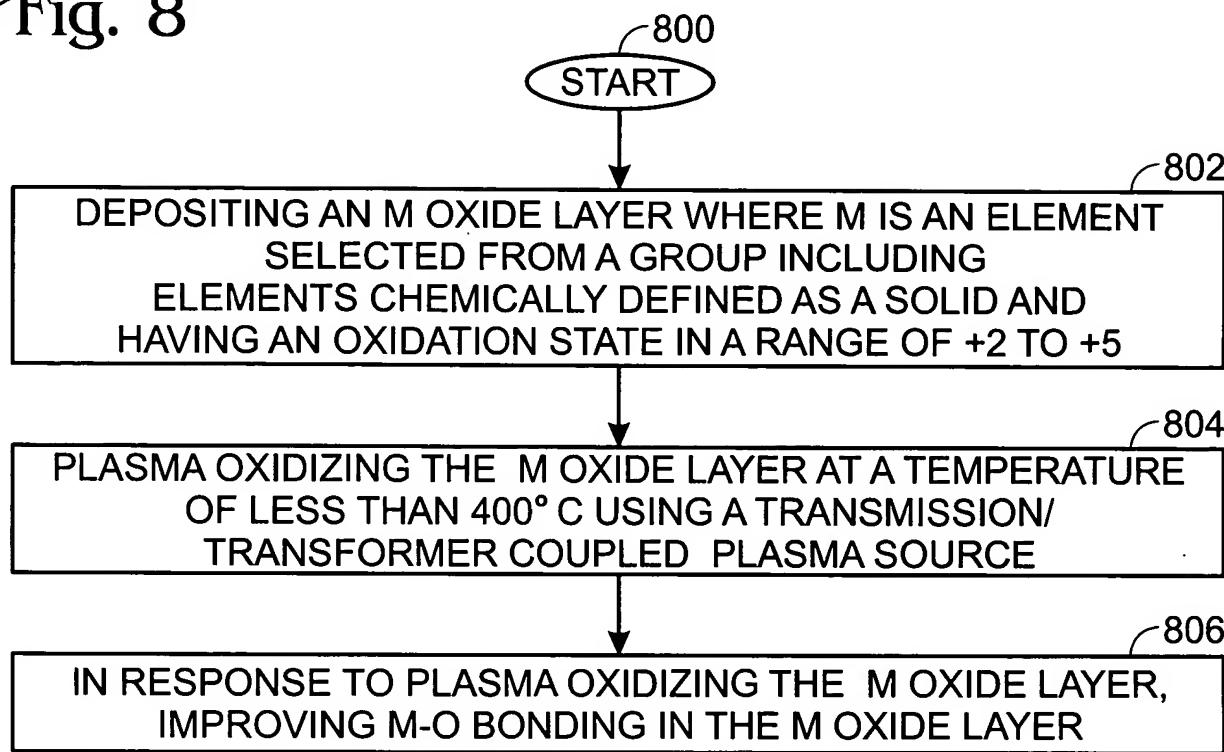


Fig. 9

